

Avionics Pulsed Power Transistor 850W, 1025-1150 MHz, 10µs Pulse, 1% Duty M/A-COM Products Released, 30 May 07

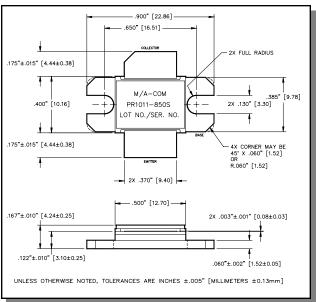
Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- · High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V _{CES}	80	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	250	Α
Power Dissipation @ +25°C	P _{TOT}	11.6	kW
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 250mA		BV _{CES}	80	-	V
Collector-Emitter Leakage Current	V _{CE} = 50V		I _{CES}	-	30	mA
Thermal Resistance	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	R _{TH(JC)}	-	0.015	°C/W
Input Power	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	P _{IN}	-	141	W
Power Gain	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	G_P	7.8	-	dB
Collector Efficiency	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	ης	42	-	%
Input Return Loss	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc=50V, Pout=850W	F = 1025 MHz	VSWR-T	-	5:1	-
Load Mismatch Stability *	Vcc=50V, Pout=850W	F = 1025, 1090, 1150 MHz	VSWR-S	-	1.5:1	-

^{*} All spurious signals shall be < -60dBc below carrier, except F = Fo ± ½ Fo shall be < -40dBc

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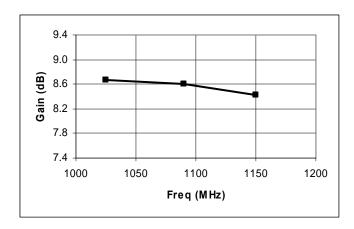
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Typical RF Performance

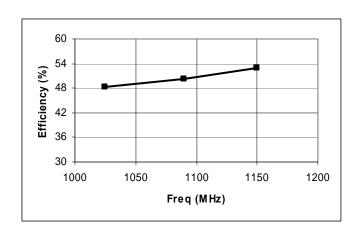
Freq.	Pin	Pout	Gain	∆Gain	lc	Eff	RL	VSWR-S	WR-S VSWR-T	P1dB Overdrive		
(MHz)	(W)	(W)	(dB)	(dB)	(A)	(%)	(dB)	(1.5:1)	(5:1)	Pout	Δ Ρο	
1025	116	850	8.67	1	35.3	48.2	-18.3	S	Р	974	0.59	
1090	117	850	8.61	-	33.9	50.3	-16.3	S	-	1014	0.76	
1150	112	850	8.42	0.25	32.1	53.0	-21.1	S	-	997	0.69	

Note: ΔPo(dB) is the difference between Pout at 1dB overdrive and Pout at Pout=850W.

Gain vs. Frequency



Collector Efficiency vs. Frequency



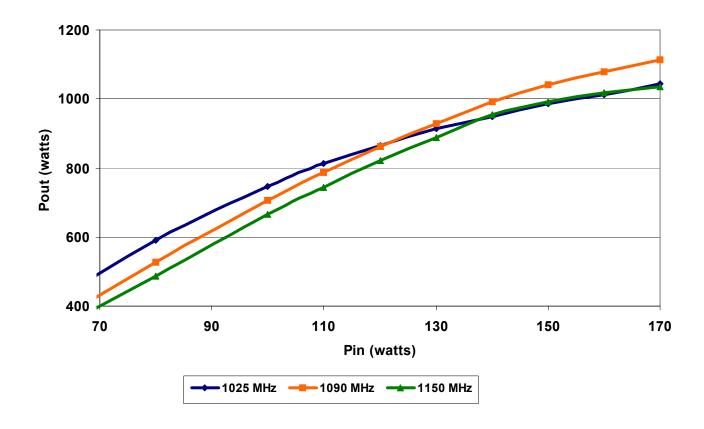
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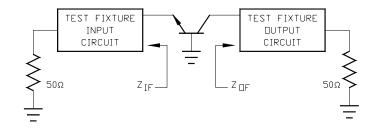
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RF Power Transfer Curve (Output Power Vs. Input Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)		
1025	1.7 - j1.8	0.8 - j1.3		
1090	1.4 - j1.2	0.8 - j1.0		
1150	1.3 - j0.7	0.8 - j0.8		



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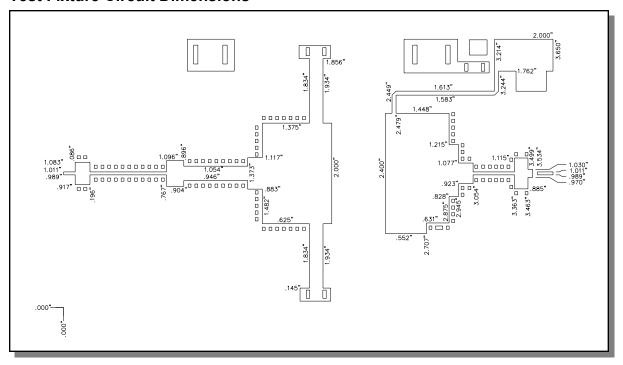
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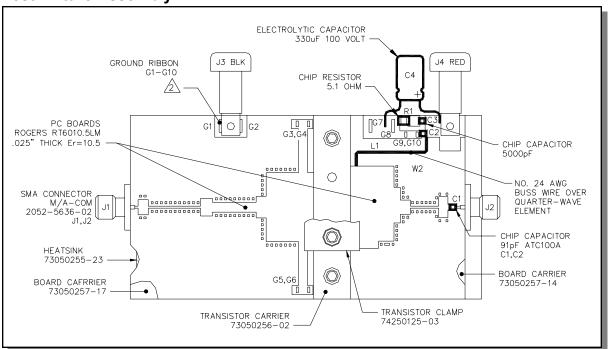


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Test Fixture Circuit Dimensions



Test Fixture Assembly



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